

FGW75N65WE

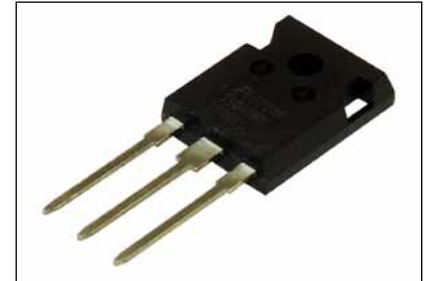
Discrete IGBT (High-Speed W series) 650V / 75A

Features

- Low power loss
- Low switching surge and noise
- High reliability, high ruggedness (RBSOA, SCSOA etc.)

Applications

- Uninterruptible power supply
- PV Power conditioner
- Inverter welding machine



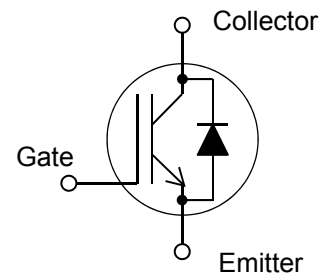
Maximum Ratings and Characteristics

Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ (unless otherwise specified)

Items	Symbols	Characteristics	Unit	Remarks
Collector-Emitter Voltage	V_{CES}	650	V	
Gate-Emitter Voltage	V_{GES}	± 20	V	$T_r < 1\mu\text{s}$
Transient Gate-Emitter Voltage		± 30		
DC Collector Current	$I_C@25$	124	A	$T_c=25^\circ\text{C}$
	$I_C@100$	75	A	$T_c=100^\circ\text{C}$
Pulsed Collector Current	I_{CP}	300	A	Note *1
Turn-Off Safe Operating Area	-	300	A	$V_{CE} \leq 650\text{V}$ $T_j \leq 175^\circ\text{C}$
Diode Forward Current	$I_F@25$	111	A	
	$I_F@100$	75	A	
Diode Pulsed Current	I_{FP}	300	A	Note *1
IGBT Max. Power Dissipation	P_{D_IGBT}	520	W	$T_c=25^\circ\text{C}$
FWD Max. Power Dissipation	P_{D_FWD}	260	W	$T_c=25^\circ\text{C}$
Operating Junction Temperature	T_j	-40 ~ +175	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-55 ~ +175	$^\circ\text{C}$	

Note *1 : Pulse width limited by T_{jmax} .

Equivalent circuit



Electrical characteristics at $T_j = 25^\circ\text{C}$ (unless otherwise specified) Static Characteristics

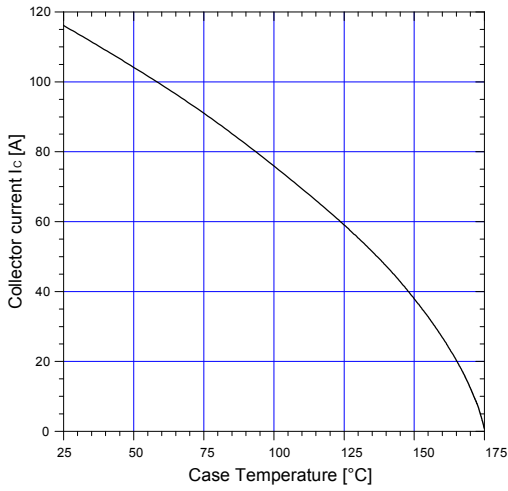
Description	Symbol	Conditions	min.	typ.	max.	Unit	
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 650\text{V}, V_{GE} = 0\text{V}$	$T_j=25^\circ\text{C}$	-	-	250	μA
			$T_j=175^\circ\text{C}$	-	-	2	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE} = 0\text{V}, V_{GE} = \pm 20\text{V}$	-	-	200	nA	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 20\text{V}, I_C = 75\text{mA}$	3.0	4.0	5.0	V	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{V}, I_C = 75\text{A}$	$T_j=25^\circ\text{C}$	-	1.80	2.20	V
			$T_j=125^\circ\text{C}$	-	2.05	-	
			$T_j=175^\circ\text{C}$	-	2.10	-	
Input Capacitance	C_{ies}	$V_{CE}=25\text{V}$	-	5300	-	pF	
Output Capacitance	C_{oes}	$V_{GE}=0\text{V}$	-	150	-		
Reverse Transfer Capacitance	C_{res}	$f=1\text{MHz}$	-	120	-		
Gate Charge	Q_G	$V_{CC} = 520\text{V}$ $I_C = 75\text{A}$ $V_{GE} = 15\text{V}$	-	300	-	nC	
Turn-On Delay Time	$t_{d(on)}$	$T_j = 25^\circ\text{C}, V_{CC} = 400\text{V}$ $I_C = 37.5\text{A}, V_{GE} = 15\text{V}$ $R_G = 10\Omega$	-	34	-	ns	
Rise Time	t_r		-	56	-		
Turn-Off Delay Time	$t_{d(off)}$		-	300	-		
Fall Time	t_f		-	110	-		
Turn-On Energy	E_{on}		-	0.95	-		mJ
Turn-Off Energy	E_{off}	-	1.2	-			
Turn-On Delay Time	$t_{d(on)}$	$T_j = 150^\circ\text{C}, V_{CC} = 400\text{V}$ $I_C = 37.5\text{A}, V_{GE} = 15\text{V}$ $R_G = 10\Omega$	-	34	-	ns	
Rise Time	t_r		-	56	-		
Turn-Off Delay Time	$t_{d(off)}$		-	340	-		
Fall Time	t_f		-	94	-		
Turn-On Energy	E_{on}		-	1.6	-		mJ
Turn-Off Energy	E_{off}	-	1.2	-			
Forward Voltage Drop	V_F	$I_F=75\text{A}$	$T_j=25^\circ\text{C}$	-	2.5	3.2	V
			$T_j=125^\circ\text{C}$	-	1.9	-	V
			$T_j=175^\circ\text{C}$	-	1.7	-	V
Diode Reverse Recovery Time	t_{rr}	$V_{CC}=400\text{V}, I_F=37.5\text{A}$	-	180	-	ns	
Diode Reverse Recovery Charge	Q_{rr}	$-di_F/dt=500\text{A}/\mu\text{s}, T_j=25^\circ\text{C}$	-	0.41	-	μC	
Diode Reverse Recovery Time	t_{rr}	$V_{CC}=400\text{V}, I_F=37.5\text{A}$	-	190	-	ns	
Diode Reverse Recovery Charge	Q_{rr}	$-di_F/dt=500\text{A}/\mu\text{s}, T_j=150^\circ\text{C}$	-	1.50	-	μC	

● Thermal Resistance

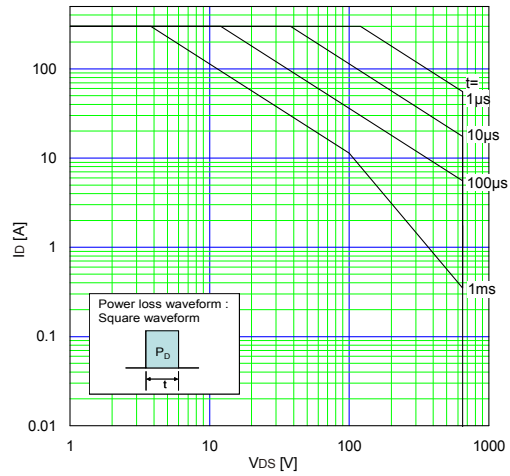
Description	Symbol	min.	typ.	max.	Unit
Thermal Resistance, Junction-Ambient	$R_{th(j-a)}$	-	-	50	°C/W
Thermal Resistance, IGBT Junction to Case	$R_{th(j-c)}_{IGBT}$	-	-	0.286	°C/W
Thermal Resistance, FWD Junction to Case	$R_{th(j-c)}_{FWD}$	-	-	0.568	°C/W

Characteristics (Representative)

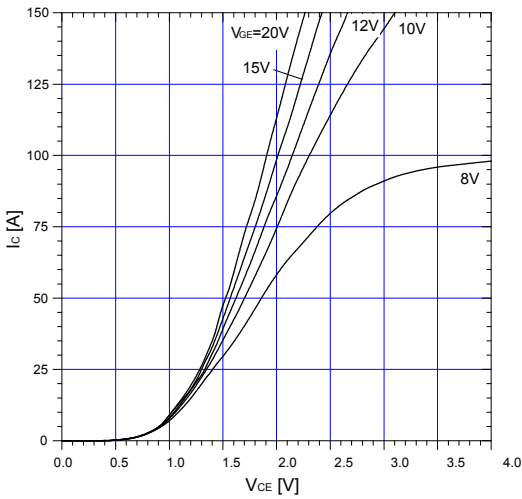
Graph.1
DC Collector Current vs Tc
 $V_{GE} \geq +15V, T_j \leq 175^\circ C$



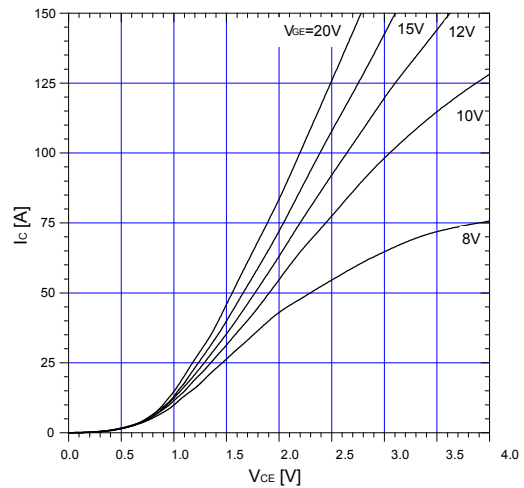
Graph.2
FBSOA
Duty=0(Single pulse), Tc=25°C



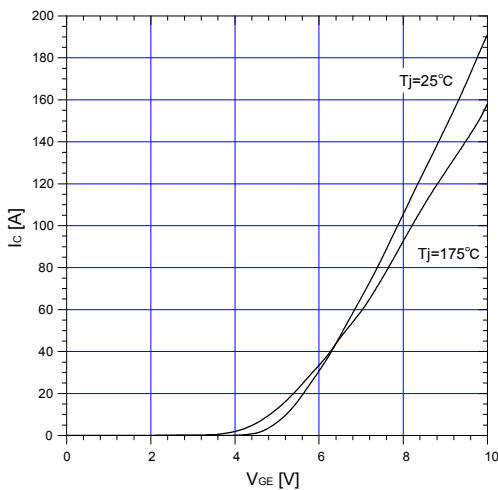
Graph.3
Typical Output Characteristics ($V_{CE}-I_c$)
 $T_j = 25^\circ C$



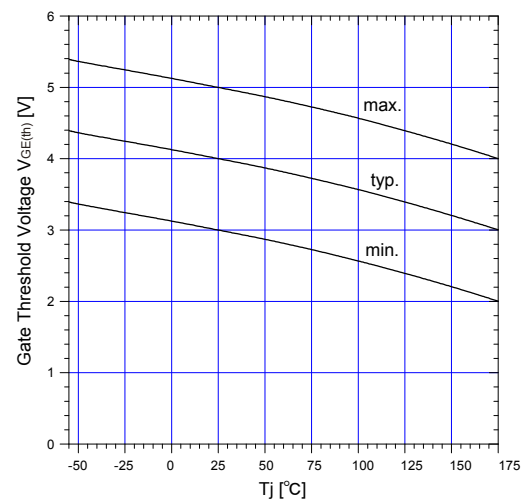
Graph.4
Typical Output Characteristics ($V_{CE}-I_c$)
 $T_j = 175^\circ C$



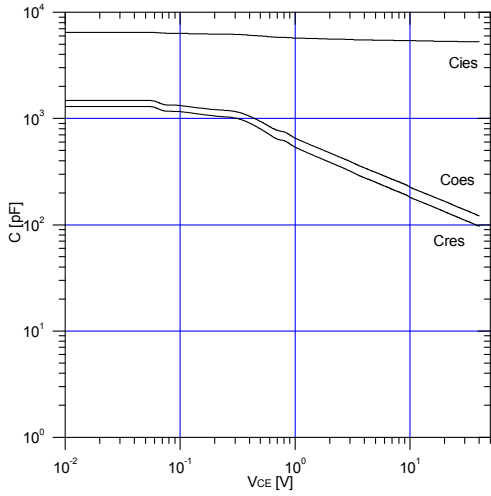
Graph.5
Typical Transfer Characteristics
 $V_{CE} = 10V$



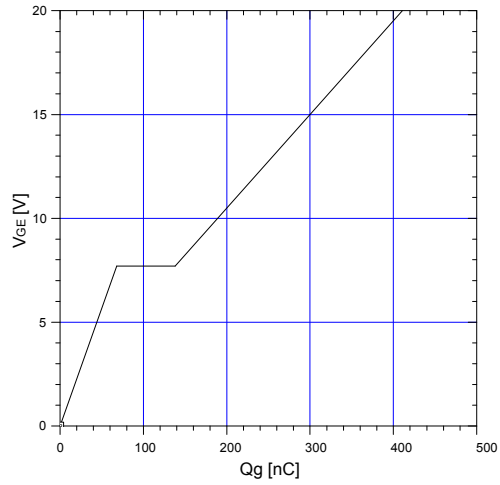
Graph.6
Gate Threshold Voltage vs. Tj
 $I_c = 75mA, V_{CE} = 20V$



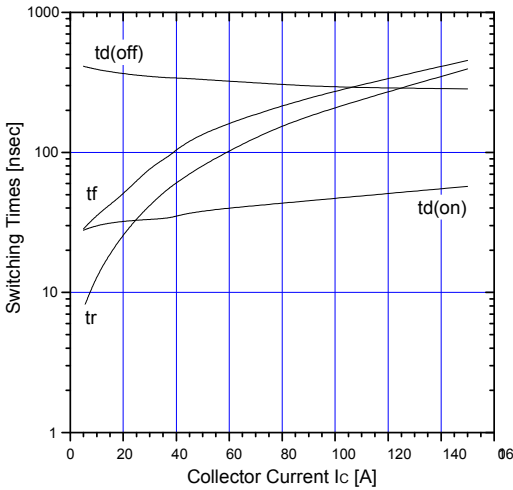
Graph.7
Typical Capacitance
 $V_{GE}=0V, f=1MHz, T_j=25^{\circ}C$



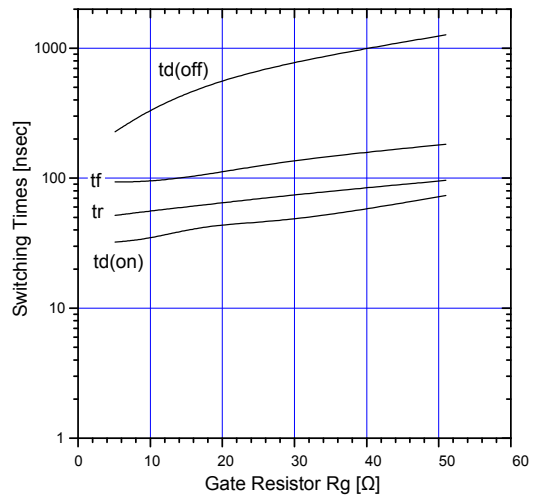
Graph.8
Typical Gate Charge
 $V_{cc}=520V, I_c=75A, T_j=25^{\circ}C$



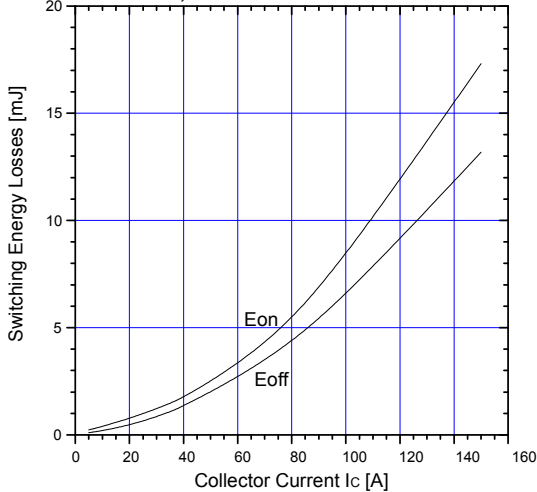
Graph.9
Typical switching time vs. Ic
 $T_j=150^{\circ}C, V_{cc}=400V, L=500\mu H$
 $V_{GE}=15V, R_G=10\Omega$



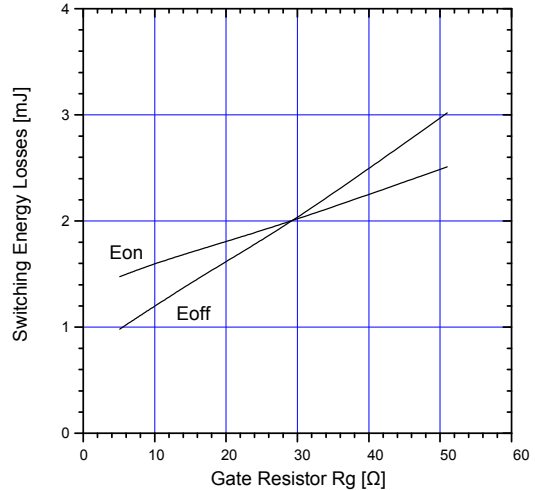
Graph.10
Typical switching time vs. Rg
 $T_j=150^{\circ}C, V_{cc}=400V, I_c=37.5A, L=500\mu H$
 $V_{GE}=15V$



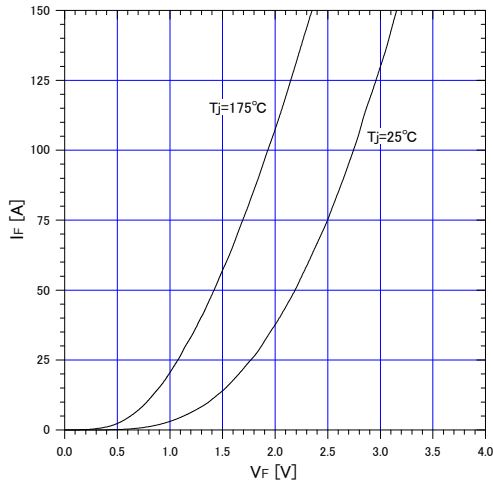
Graph.11
Typical switching losses vs. Ic
 $T_j=150^{\circ}C, V_{cc}=400V, L=500\mu H$
 $V_{GE}=15V, R_G=10\Omega$



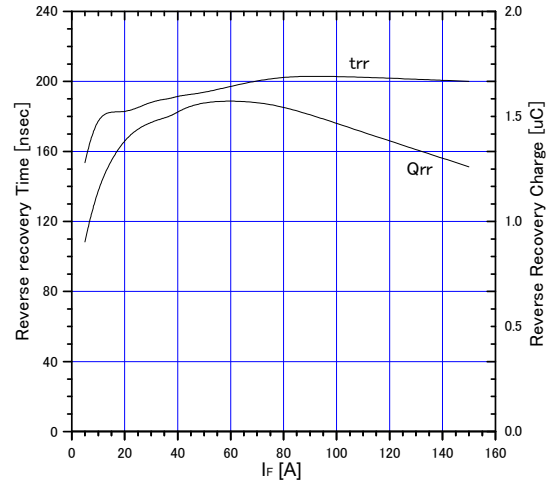
Graph.12
Typical switching losses vs. Rg
 $T_j=150^{\circ}C, V_{cc}=400V, I_c=37.5A, L=500\mu H$
 $V_{GE}=15V$



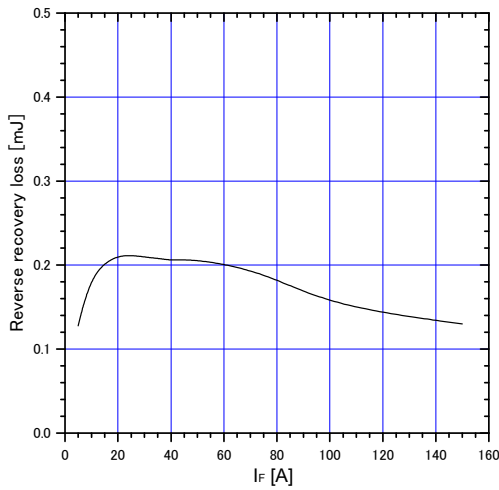
Graph.13
FWD Forward voltage drop (V_F - I_F)



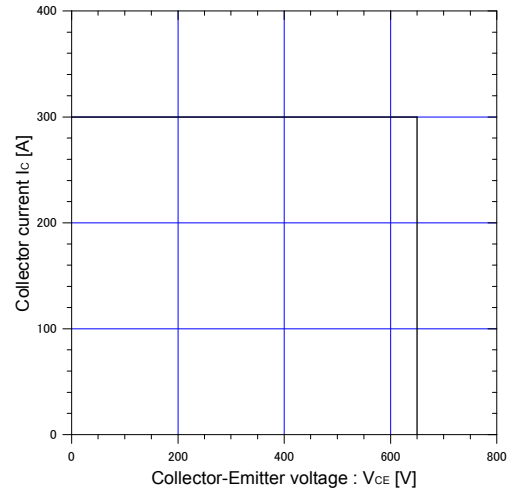
Graph.14
Typical reverse recovery characteristics vs. I_F
 $T_j=15^\circ\text{C}$, $V_{CC}=400\text{V}$, $L=500\mu\text{H}$
 $V_{GE}=15\text{V}$, $R_G=10\Omega$



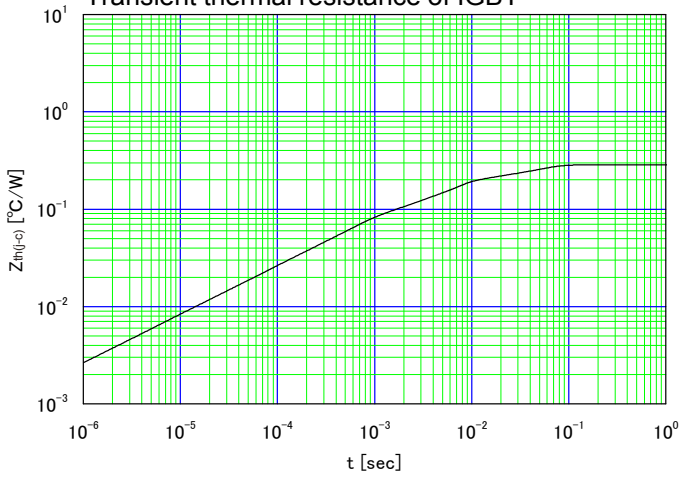
Graph.15
Typical reverse recovery loss vs. I_F
 $T_j=150^\circ\text{C}$, $V_{CC}=400\text{V}$, $L=500\mu\text{H}$
 $V_{GE}=15\text{V}$, $R_G=10\Omega$



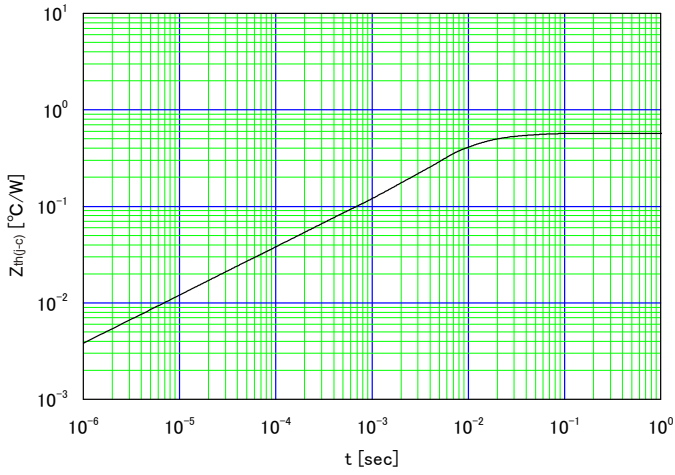
Graph.16
Reverse biased Safe Operating Area
 $T_j \leq 175^\circ\text{C}$, $V_{GE}=+15\text{V}/0\text{V}$, $R_G=10\Omega$



Graph.17
Transient thermal resistance of IGBT

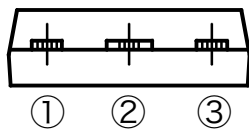
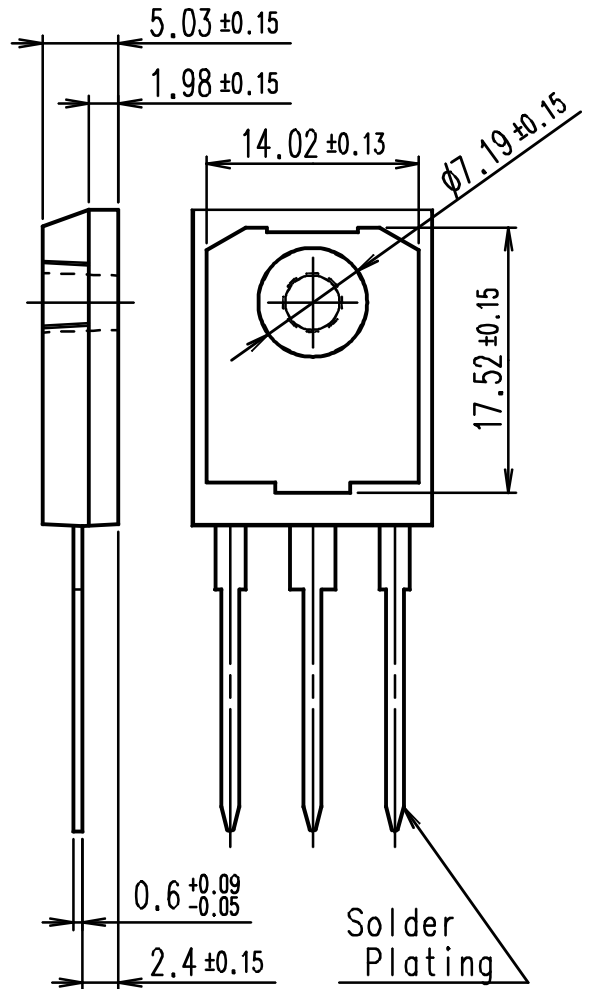
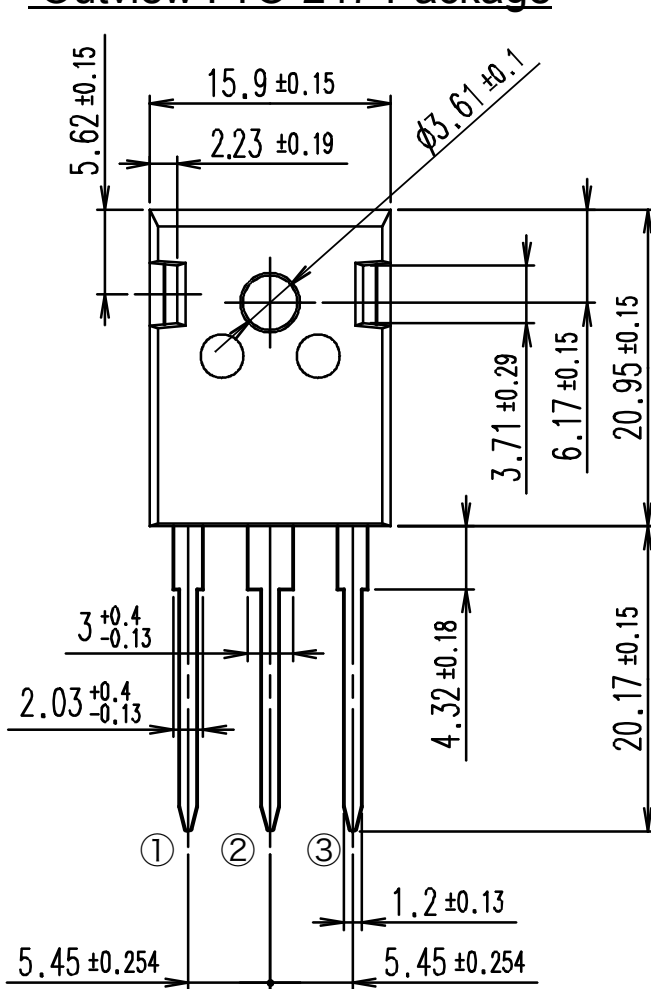


Graph.18
Transient thermal resistance of FWD



■ Outline Drawings, mm

Overview : TO-247 Package



CONNECTION

- ① GATE
- ② COLLECTOR
- ③ EMITTER

DIMENSIONS ARE IN MILLIMETERS.

WARNING

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IGBT Modules

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